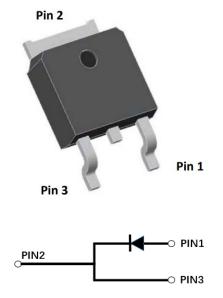


YJD106510DQG2Q

Silicon Carbide Schottky Diode

V _{RRM}	650V
I _F (135°C)	14A
Q _C	30nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- AEC-Q101 qualified
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, automotive battery chargers.

Mechanical Data

- Package: TO-252 Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free
- Terminals: Tin plated leads
- Polarity: As marked

■Maximum Ratings (T_c=25[°]C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D106510DQG2
Reverse voltage (repetitive peak) @ T _j =25°C	V _{RRM}	V	650
Reverse voltage (Surge Peak) @ T _j =25°C	V _{RSM}	V	650
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	650
Continuous forward current @ T _c =25°C			32
Continuous forward current @ T _c =135°C	I _F	А	14
Continuous forward current @ T _c =154°C			10
Non-repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	70
Power Dissipation@ T _c =25°C	Ρτοτ	w	132
Power Dissipation@ T _c =110°C	F TOT	vv	57
i²t Value@ Tc=25°C ,tp=10ms	∫ i²dt	A ² S	32
Operating junction and Storage temperature range	T _j ,T _{stg}	°C	-55 to +175

Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.			
Forward valtage drap	N	/ _F V	I _F =10A, T _j =25°C	1.35	1.55			
Forward voltage drop	VF		I _F =10A, T _j =175°C	1.8	-			
Reverse leakage current	I _R μA	I _R μA	V _R =650V, T _j =25°C	0.5	25			
Neverse leakage current			V _R =650V, T _j =175°C	2	-			
Total capacitive charge	Qc	nC	V_R =400V, T _j =25°C , QC= \int_0^{VR} C(V)dV	30	-			
	capacitance C pF					V _R =0V, f=1MHZ	543	-
Total capacitance		pF	V _R =200V, f=1MHZ	55	-			
			V _R =400V, f=1MHZ	52	-			
Capacitance Stored Energy	Ec	μJ	V _R =400V	3.7	-			

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	R _{eJ-C}	°C W	1.14

■Typical Characteristics

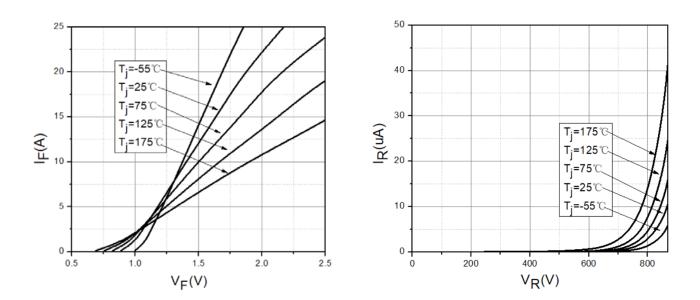


Figure 1. Forward Characteristics

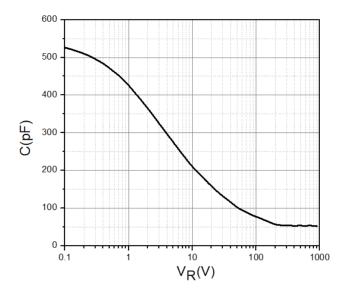
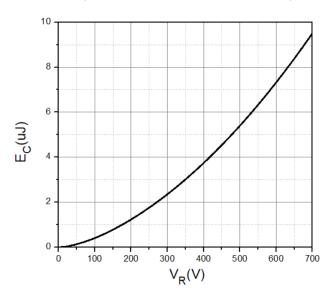


Figure 3. Capacitance vs. Reverse Voltage



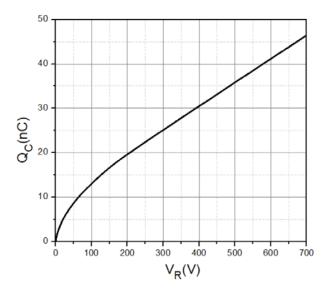
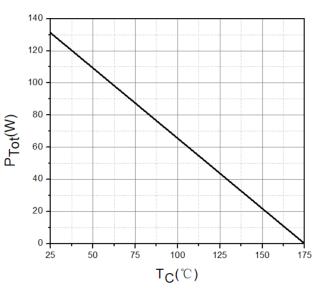
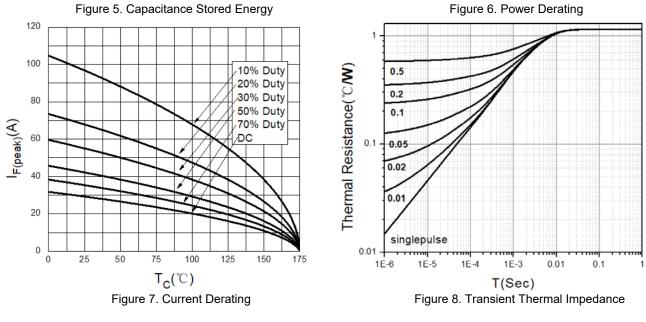


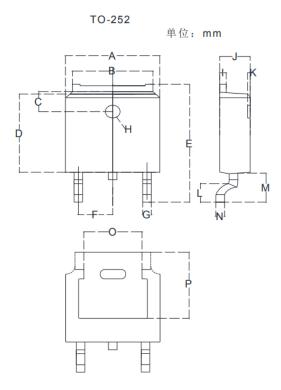
Figure 4. Total Capacitance Charge vs. Reverse Voltage







Outline Dimensions



TO-252			
Dim	Min	Max	
Α	6.500	6.700	
В	5.100	5.460	
С	1.400	1.800	
D	6.000	6.200	
Е	10.000	10.400	
F	2.166	2.366	
G	0.660	0.860	
Н	Φ 1.050	Ф 1.350	
I.	0.460	0.580	
J	2.200	2.400	
К	0	0.300	
L	0.890	2.290	
М	2.730	3.080	
Ν	0.430	0.580	
0	4.20	4.95	
Р	5.15	5.45	



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